

IN THE SPECIFICATION:

Please replace paragraph 0028 with the following amended paragraph:

[0028] Any known solid precursor typically used in the production of semiconductor wafers can be used. Suitable preferred examples include $W(CO)_6$ and TaO_x precursors. The solid precursor may be applied to the surface by any means that will permit it to remain thereon. For example, the solid precursor may be pressed onto the surface to increase surface area for vaporization. This is an improvement over prior apparatus and methods, where vaporization was limited to the top surfaces of a solid material located in the bottom of a container. Alternatively, solid precursors may be dissolved in solution and the heating element may be dipped into the solution. After it is allowed to dry, the solid is retained on the heating element. A rough surface on the heating element may ~~improves~~ improve adhesion of the solid precursor to the heating element.

Please replace paragraph 0030 with the following amended paragraph:

[0030] To vaporize a solid precursor using the apparatus set forth in Figure 1, a solid precursor is first applied to surface 6. The said precursor can be applied by pressing the precursor onto surface 6 or by "dipping" the heating element into the dissolved precursor as discussed above. The solid precursor is then heated, either directly by heating member 8 located inside surface 6, or indirectly by heating element 8 located inside the walls of housing 2, until a temperature high enough to vaporize the solid precursor is reached. The vaporization temperature will vary depending on the solid ~~substrate~~ precursor applied to surface 6. A carrier gas enters housing 2 through inlet 4 and carries the vaporized solid precursor to a reaction chamber (not shown) via outlet 11. Once the vaporized precursor reaches the reaction chamber, it is deposited onto the surface of a substrate (e.g., semiconductor wafer) by conventional deposition methods such as atomic layer deposition (ALD), chemical vapor deposition methods (CVD), and evaporative coating (i.e., the redeposition of substance from precursor onto wafer or substrate).